CLAIMS

What is claimed is:

- 1. An integrated circuit, comprising:
 - a plurality of switches;
- a first conductor having a first span along a first dimension, wherein the first conductor selectively couples to at least one input of each of at least two adjacent program controlled cells through a respective switch of the plurality of switches without requiring traversal of another conductor;
- a second conductor and a third conductor having two different spans in the first dimension, wherein the first conductor selectively couples to the second conductor and the third conductor; and
- a fourth conductor and a fifth conductor having two different spans in a second dimension, wherein each of the fourth conductor and the fifth conductor drives the first conductor through a respective independently controlled switch of the plurality of switches.
- 2. The integrated circuit of claim 1, wherein each of the plurality of switches comprises at least a program controlled passgate.

- 3. The integrated circuit of claim 1, wherein each of the plurality of switches comprises at least a program controlled driver/receiver.
- 4. The integrated circuit of claim 1, wherein the plurality of switches comprise at least one of a program controlled passgate and a program controlled driver/receiver.
- 5. The integrated circuit of claim 1, wherein one of the plurality of switches has a program controlled on state and off state.
- 6. The integrated circuit of claim 1, wherein the integrated circuit is implemented using process technology incorporating memory devices.
- 7. The integrated circuit of claim 1, wherein the integrated circuit is implemented using process technology incorporating non-volatile memory devices.
- 8. The integrated circuit of claim 1, wherein the integrated circuit is implemented using process technology incorporating fuse devices.

- 9. The integrated circuit of claim 1, wherein the integrated circuit is implemented using process technology incorporating anti-fuse devices.
- 10. The integrated circuit of claim 1, wherein the integrated circuit is implemented using process technology incorporating Ferro-electric devices.
- 11. A method of operating an integrated circuit, comprising:

providing a plurality of switches;

providing a first conductor having a first span along a first dimension;

selectively coupling the first conductor to at least one input of each of at least two adjacent program controlled cells through a respective switch of the plurality of switches without requiring traversal of another conductor;

providing a second conductor and a third conductor having two different spans in the first dimension;

selectively coupling the first conductor to the second conductor and the third conductor;

providing a fourth conductor and a fifth conductor having two different spans in a second dimension; and

driving the first conductor using each of the fourth and the fifth conductors through a respective independently controlled switch of the plurality of switches.

- 12. The method of claim 11, wherein each of the plurality of switches comprises at least a program controlled passgate.
- 12. The method of claim 11, wherein each of the plurality of switches comprises at least a program controlled driver/receiver.
- 13. The method of claim 11, wherein the plurality of switches comprise at least one of a program controlled passgate and a program controlled driver/receiver.
- 14. The method of claim 11, wherein one of the plurality of switches has a program controlled on state and off state.

- 15. The method of claim 11, wherein the integrated circuit is implemented using process technology incorporating memory devices.
- 16. The method of claim 11, wherein the integrated circuit is implemented using process technology incorporating non-volatile memory devices.
- 17. The method of claim 11, wherein the integrated circuit is implemented using process technology incorporating fuse devices.
- 18. The method of claim 11, wherein the integrated circuit is implemented using process technology incorporating antifuse devices.
- 19. The method of claim 11, wherein the integrated circuit is implemented using process technology incorporating Ferro-electric devices.